

ZXTN5551Z 160V, SOT89, NPN high voltage transistor

Summary

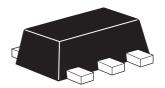
BV_{CEO} > 160V

 $BV_{EBO} > 6V$

 $I_{C(cont)} = 600 mA$

 $P_{D} = 1.2W$

Complementary part number ZXTP5401Z

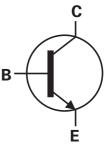


Description

A high voltage NPN transistor in a small outline surface mount package

Features

- 160V rating
- SOT89 package

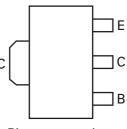


Applications

· High voltage amplification

Ordering information

| Device | Reel size (inches) | Tape width (mm) | Quantity per reel |
|-------------|-----------------------|-----------------|-------------------|
| ZXTN5551ZTA | 7 | 12 | 1000 |



Pinout - top view

Device marking

N51

Absolute maximum ratings

| Parameter | Symbol | Limit | Unit | |
|--|-----------------------------------|------------|-------|--|
| Collector-base voltage | V _{CBO} | 180 | V | |
| Collector-emitter voltage | V _{CEO} | 160 | V | |
| Emitter-base voltage | V _{EBO} | 6 | V | |
| Continuous collector current ^(a) | I _C | 600 | mA | |
| Power dissipation at T _A =25°C ^(a) | P _D | 1.2 | W | |
| Linear derating factor | | 9.6 | mW/°C | |
| Operating and storage temperature range | T _j , T _{stg} | -55 to 150 | °C | |

Thermal resistance

| Parameter | Symbol | Value | Unit |
|------------------------------------|-----------------|-------|------|
| Junction to ambient ^(a) | $R_{\Theta JA}$ | 104 | °C/W |

NOTES:

(a) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

Electrical characteristics (at $T_{amb} = 25$ °C unless otherwise stated).

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|---|----------------------|------|------|------|------|--|
| Collector-base breakdown voltage | BV _{CBO} | 180 | 270 | | V | $I_C = 100 \mu A$ |
| Collector-emitter breakdown voltage (base open) | BV _{CEO} | 160 | 200 | | V | I _C = 1mA ^(*) |
| Emitter-base breakdown voltage | BV _{EBO} | 6 | 7.85 | | V | $I_E = 10 \mu A$ |
| Collector cut-off current | I _{CBO} | | <1 | 50 | nA | V _{CB} = 120V |
| | | | | 50 | μΑ | $V_{CB} = 120V, T_{amb} = 100^{\circ}C$ |
| Collector-emitter | V _{CE(sat)} | | 65 | 150 | mV | $I_C = 10 \text{mA}, I_B = 1 \text{mA}^{(*)}$ |
| saturation voltage | | | 115 | 200 | mV | $I_C = 50 \text{mA}, I_B = 5 \text{mA}^{(*)}$ |
| Base-emitter saturation | V _{BE(sat)} | | 760 | 1000 | mV | I _C = 10mA, I _B = 1mA ^(*) |
| voltage | | | 840 | 1200 | mV | $I_C = 50 \text{mA}, I_B = 5 \text{mA}^{(*)}$ |
| Static forward current | h _{FE} | 80 | 130 | | | I _C = 1mA, V _{CE} = 5V ^(*) |
| transfer ratio | | 80 | 145 | 250 | | $I_C = 10 \text{mA}, V_{CE} = 5 V^{(*)}$ |
| | | 30 | 65 | | | $I_C = 50 \text{mA}, V_{CE} = 5V^{(*)}$ |
| Transition frequency | f _T | | 130 | | MHz | I _C = 10mA, V _{CE} = 10V f = 100MHz |
| Output capacitance | C _{OBO} | | | 6 | pF | V _{CB} = 10V, f = 1MHz ^(*) |
| Small signal | h _{FE} | 50 | | 260 | | I _C = 10mA, V _{CE} = 10V, f=1kHz ^(†) |
| Delay time | t _(d) | | 95 | | ns | $V_{CC} = 10V. I_{C} = 10mA,$ |
| Rise time | t _(r) | | 64 | | ns | $I_{B1} = I_{B2} = 1 \text{mA}.$ |
| Storage time | t _(s) | | 1256 | | ns | |
| Fall time | t _(f) | | 140 | | ns | |

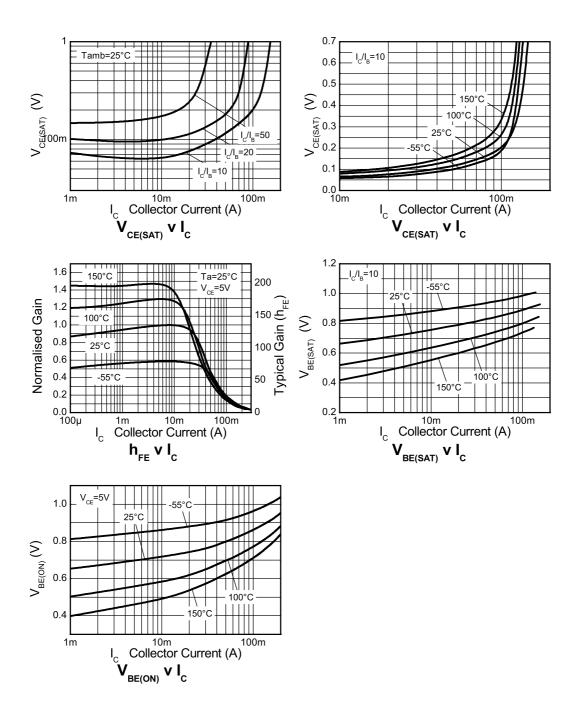
NOTES:

^(*) Measured under pulsed conditions. Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$.

^(†) Periodic sample test only



Typical characteristics



ZXTN5551Z

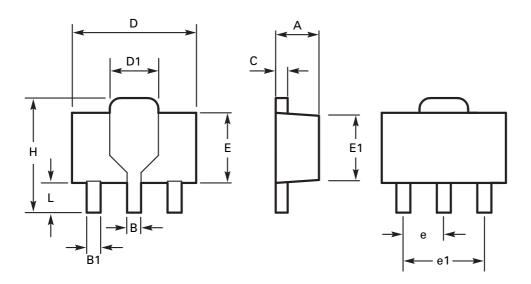
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Package outline - SOT89



| DIM | Millin | neters | Inc | hes | DIM | Millimeters | | Inches | |
|-----|--------|--------|-------|-------|-----|-------------|------|--------|-------|
| | Min | Max | Min | Max | | Min | Max | Min | Max |
| Α | 1.40 | 1.60 | 0.550 | 0.630 | Е | 2.29 | 2.60 | 0.090 | 0.102 |
| В | 0.44 | 0.56 | 0.017 | 0.022 | E1 | 2.13 | 2.29 | 0.084 | 0.090 |
| B1 | 0.36 | 0.48 | 0.014 | 0.019 | е | 1.50 BSC | | 0.059 | BSC |
| С | 0.35 | 0.44 | 0.014 | 0.017 | e1 | 3.00 BSC | | 0.118 | BSC |
| D | 4.40 | 4.60 | 0.173 | 0.181 | Н | 3.94 | 4.25 | 0.155 | 0.167 |
| D1 | 1.52 | 1.83 | 0.064 | 0.072 | L | 0.89 | 1.20 | 0.035 | 0.047 |

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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